TOSHIBA {DISCRETE/OPTO}
查询MG15G6EM1供应商
19097250 TOSHIBA (DISCRETE/OPTO)



1 A M G Ŋ G 1

SEMICONDUCTOR

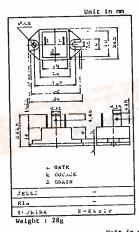
TECHNICAL DATA

90 DE 9097250 0016394 3 捷多邦,专业PCB打样工厂,24小时加急出货 900 16394 D 7-77-27

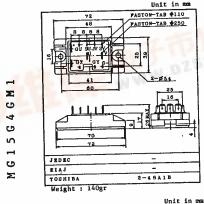
MG15G1AM1 M G 1 5 G 4 G M 1 (450V/15A) M G 1 5 G 6 E M 1

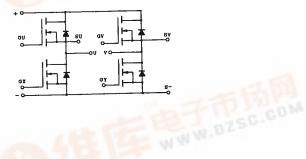
EQUIVALENT CIRCUIT

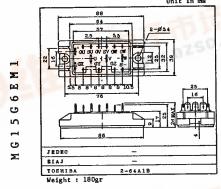


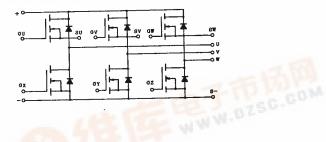












TOSHIBA CORPORATION - 402 -

GT1A2A



9097250 TOSHIBA (DISCRETE/OPTO)

90D 16395 DT-39-27



SEMICONDUCTOR

TECHNICAL DATA

M G 1 5 G 1 A M 1 M G 1 5 G 4 G M 1 M G 1 5 G 6 E M 1

MAXIMUM RATINGS (Ta=25°C)

CHARACTER ISTIC		SYMBOL	RATING	UNIT	
Drain-Source Voltage		VDSS	450	v	
Gate-Source Voltage		VGSS	±20	v	
	DC	_	· ±15	A	
Drain Current	Peak	I _D	±30		
Drain Power Dissipation (Tc=25°C)		PD	125	W	
Channel Temperature		Tch	150	°c	
Storage Temperature Range		Tstg	-40 ~ 125	°c	
Isolation Voltage		Visol	2500 (AC 1 Minute)	v	
Screw Torque		_	30	kg · cm	

ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		IGSS	V _{GS} =±20V, V _{DS} =0	-	-	±100	nA
Drain Cut-off Current		IDSS	V _{DS} =450V, V _{GS} =0	-	_	1.0	mA
Drain-Source Breakdown Voltage		V(BR)DSS	ID=10mA, VGS=0	450	-	-	v
Gate Threshold Voltage		Vth	V _{DS} =10V, I _D =1mA	1.5	-	3.5	v
Forward Transfer Admittance		Yfs	V _{DS} =10V, I _D =15A	4.0	7.0	- ·	S
Drain-Source ON Resistance		RDS (ON)	I _D =15A, V _{GS} =10V	-	-	0.4	Ω
Source Drain Forward Voltage		VSDF	I _D =-15A, V _G S=0	-	-	1.8	V
Input Capacitance		Ciss	V _{DS} =10V, V _{GS} =0, f=1MHz	-	4500	-	pF
Switching Time	Rise Time	tr	1 _D =15A	-	250	500	ns
	Turn-on Time	ton	VIN CONT	-	300	600	ns
	Fall Time	tf	v _{nD} ≑300v	_	250	500	ns
	Turn-off Time	toff	V _{IN} :t _r ,t _f <51:8 D,C≤1%(:.OUT=50Ω'	_	1000	2000	ns
Reverse Recovery Time		trr	I _D =-15A, R _G =220Ω V _G S=-15V, di/dt=60A/μs	_	300	600	ns

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	IUSHIDA	CORPORATION	
GT 1 A 2 A	-		

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9097250 TOSHIBA (DISCRETE/OPTO)



SEMICONDUCTOR

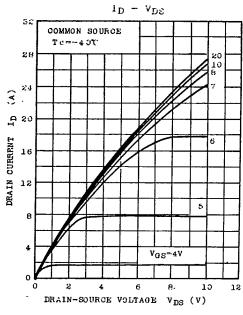
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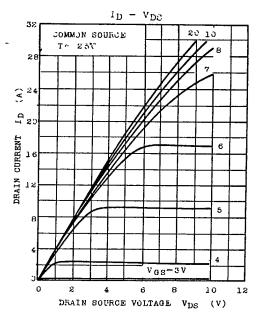
90D 16396

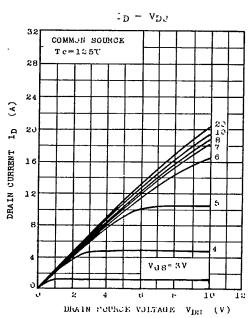
DT-39-27

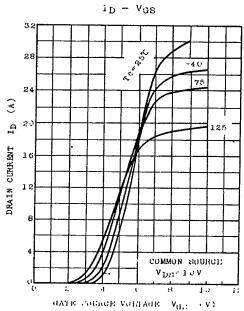
MG15G1AM1

M G 1 5 G 4 G M 1 MG15G6EM1



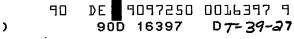






TOSHIBA CORPORATION

GT 1 A 2 A

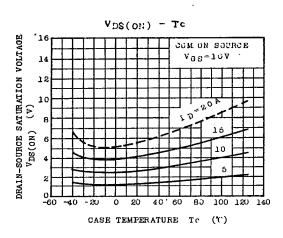


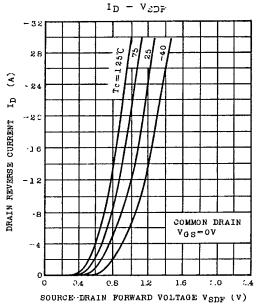


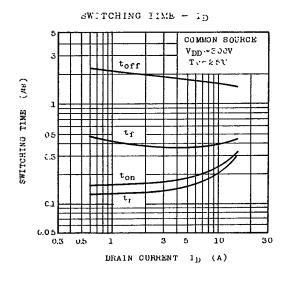
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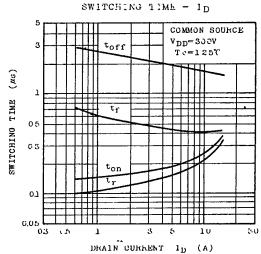
TECHNICAL DATA

M G 1 5 G 1 A M 1 M G 1 5 G 4 G M 1 M G 1 5 G 6 E M 1









TOSHIBA CORPORATION

GT 1 A 2 A

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TOSHIBA {DISCRETE/OPTO}

9097250 TOSHIBA (DISCRETE/OPTO)



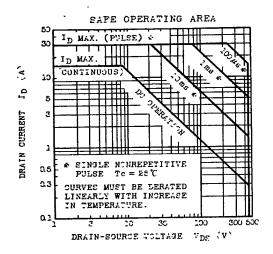
SEMICONDUCTOR

TECHNICAL DATA

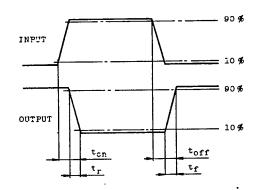
90 DE 9097250 0016398 0 900 16398 DT-39-27

M G 1 5 G 1 A M 1 M G 1 5 G 4 G M 1

MG15G6EM1



SWITCHING TIME TEST (WAVEFROM)



TOSHIBA CORPORATION

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90D 16399

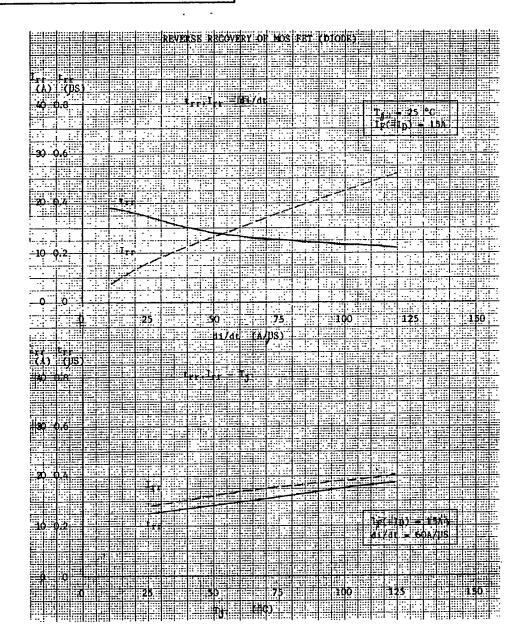
DT-39-27



SEMICONDUCTOR TECHNICAL DATA

9097250 TOSHIBA (DISCRETE/OPTO)

MG15G1AM1 MG15G4GM1 MG15G6EM1



TOSHIBA CORPORATION

GT1A2A

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9097250 TOSHIBA (DISCRETE/OPTO)

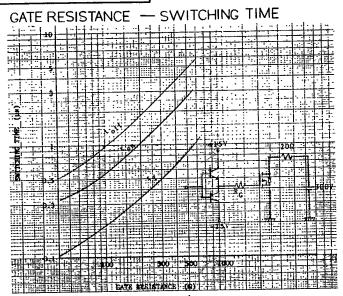
DT-39-27 90D 16400

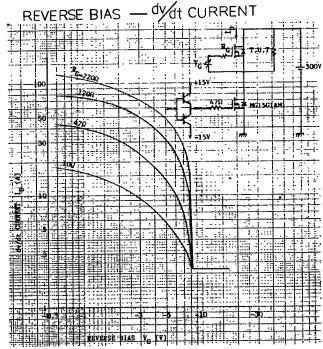


SEMICONDUCTOR

TECHNICAL DATA

MGI5GIAM I MGI5G4GMI MGI5G6EM I





TOSHIBA CORPORATION

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